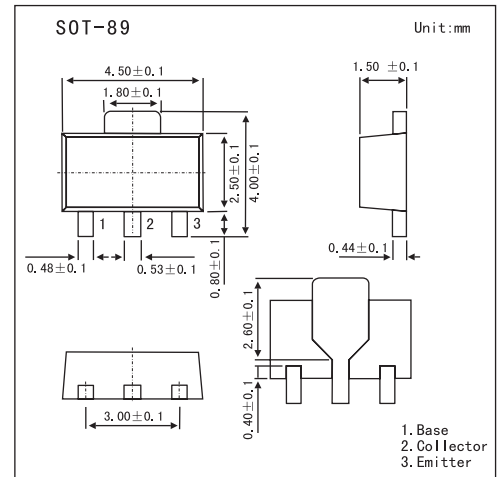


PNP Silicon Power Switching Transistor

FCX790A

■ Features

- 2W power dissipation.
- 6A peak pulse current.
- Excellent HFE characteristics.
- Low saturation voltage.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-50	V
Collector-emitter voltage	V_{CE0}	-40	V
Emitter-base voltage	V_{EB0}	-5	V
Continuous collector current	I_{CM}	-6	A
Peak pulse current	I_C	-2	A
Power dissipation	P_{tot}	1	W
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

FCX790A

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=-100μA	-50			V
Collector-emitter breakdown voltage *	V(BR)CEO	IC=-10mA	-40			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA	-5			V
Collector-base cut-off current	ICBO	VCE=-10V			0.1	μA
Emitter Cut-Off Current	IEBO	VEB=-4V			0.1	μA
Collector-emitter saturation voltage *	VCE(sat)	IC=-0.5A, IB=-5mA IC=-1A, IB=-10mA IC=-2A, IB=-50mA			-250 -350 -450	mV
Base-emitter saturation voltage *	VBE(sat)	IC=-1A, IB=-10mA			-0.9	V
Base-emitter ON voltage *	VBE(on)	IC=-1A, VCE=-2V		-0.8		V
Static Forward Current Transfer Ratio *	hFE	IC=-10mA, VCE=-2V IC=-500mA, VCE=-2V IC=-1A, VCE=-2V IC=-2A, VCE=-2V	300 250 200 150	800		
Transitional frequency	fT	IC=-50mA, VCE=-5V, f=50MHz	100			MHz
Input capacitance	Cibo	VEB=0.5V, f=1MHz		225		pF
Output capacitance	Cobo	VCE=-10V, f=1MHz		24		pF
Turn-on time	t(on)	IC=-500mA, VCC=-10V		35		ns
Turn-off time	t(off)	IB1=IB2=-50mA		600		ns

* Pulse test: tp = 300 μs; d ≤ 0.02.

■ Marking

Marking	790
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